



Bipolar PNP Bare Die – BTP033

Part Description

The BTP033 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. NPN complement is BTN033

Key Parameters:

- VCBO = -100V
- VCEO = -100V
- VEBO = -5V
- hFE = 10-50 @ VCE = -4V, IC = -3A
- VCE(Sat) = -1.2V @ IC = -3A, IB = -375mA
- fT = 3 MHz @ VCE = -10V, IE = 0A
- COBO = - pF @ VCB = - V

Features

Low VCE(sat). Designed to provide performance equivalent to CJD32C or TIP32C

Die Size (Unawn)

1430 μ m X 1430 μ m, 56 Mils X 56 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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